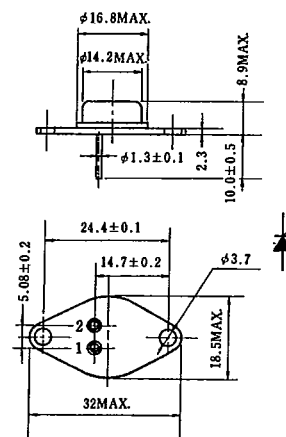


SF10G14**400V 10A****MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SF10B14	V _{DRM}	100
	SF10D14		200
	SF10G14	V _{RRM}	400
Non-Repetitive Peak Reverse Voltage (Non-Rep <5ms) T _j =0~100°C	SF10B14	V _{RSM}	150
	SF10D14		300
	SF10G14		500
Average On-State Current (Half Sine Waveform T _c =75°C)	I _{T(AV)}	10	A
R.M.S On-State Current	I _{T(RMS)}	15	A
Peak One Cycle Surge On-State Current (Non-Repetitive)	I _{TSM}	150(50Hz)	A
I ² t Limit Value (t=1ms~10ms)	I ² t	110	A ² s
Peak Forward Gate Voltage	V _{FGM}	10	V
Peak Gate Power Dissipation	P _{GM}	5	W
Average Gate Power Dissipation	P _{G(AV)}	0.5	W
Peak Forward Gate Current	I _{GM}	2	A
Peak Reverse Gate Voltage	V _{RGM}	-5	V
Junction Temperature	T _j	-40~125	°C
Storage Temperature Range	T _{stg}	-40~125	°C



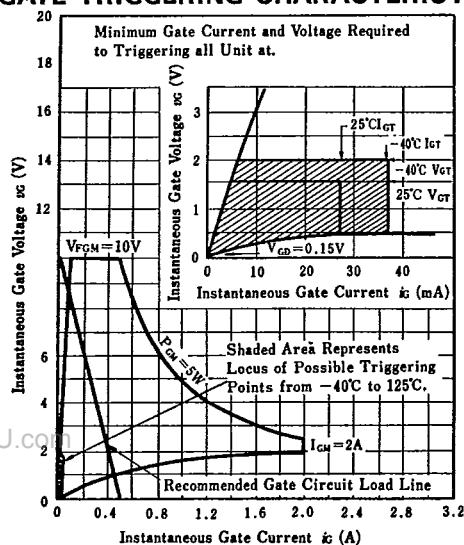
1. GATE
2. CATHODE
3. ANODE (CASE)

JEDEC TO-66
EIAJ TC-16A, TB-23
TOSHIBA 13-14A1A

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I _{DRM} and I _{RRM}	V _{DRM} =V _{RRM} =Rated, T _j =125°C	—	—	1.0	mA
Peak On-State Voltage	V _{TM}	I _{TM} =30A, T _c =25°C	—	—	1.8	V
Gate Trigger Current	I _{GT}	V _D =6V, R _L =100Ω, T _c =25°C	—	—	27	mA
Gate Trigger Voltage	V _{GT}	V _D =6V, R _L =100Ω, T _c =25°C	—	—	1.5	V
Gate Non-Trigger Voltage	V _{GD}	V _D =Rated, T _c =125°C	0.2	—	—	V
Critical Rate of Rise of Off-State Voltage	dv/dt	V _{DRM} =Rated, T _j =125°C, Exponential rise	20	—	—	V/μs
Holding Current	I _H	R _L =100Ω, T _c =25°C	—	—	60	mA
Thermal Resistance*	R _{th(j-c)}	DC	—	—	2.0	°C/W

* Junction to Case

GATE TRIGGERING CHARACTERISTICS**T_c MAX - I_{T(AV)}**